

Maurice S Skolnick

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613
papers

20,790
citations

72
h-index

119
g-index

676
ext. papers

22,791
ext. citations

4.4
avg, IF

6.16
L-index

#	Paper	IF	Citations
613	Angle-resonant stimulated polariton amplifier. <i>Physical Review Letters</i> , 2000 , 84, 1547-50	7.4	650
612	Strong exciton-photon coupling in an organic semiconductor microcavity. <i>Nature</i> , 1998 , 395, 53-55	50.4	636
611	Inverted electron-hole alignment in InAs-GaAs self-assembled quantum dots. <i>Physical Review Letters</i> , 2000 , 84, 733-6	7.4	433
610	Collective fluid dynamics of a polariton condensate in a semiconductor microcavity. <i>Nature</i> , 2009 , 457, 291-5	50.4	429
609	Strong coupling phenomena in quantum microcavity structures. <i>Semiconductor Science and Technology</i> , 1998 , 13, 645-669	1.8	410
608	Observation of a many-body edge singularity in quantum well luminescence spectra. <i>Physical Review Letters</i> , 1987 , 58, 2130-2133	7.4	377
607	Continuous wave observation of massive polariton redistribution by stimulated scattering in semiconductor microcavities. <i>Physical Review Letters</i> , 2000 , 85, 3680-3	7.4	363
606	Exciton-polaritons in van der Waals heterostructures embedded in tunable microcavities. <i>Nature Communications</i> , 2015 , 6, 8579	17.4	275
605	Room Temperature Polariton Emission from Strongly Coupled Organic Semiconductor Microcavities. <i>Physical Review Letters</i> , 1999 , 82, 3316-3319	7.4	274
604	Persistent currents and quantized vortices in a polariton superfluid. <i>Nature Physics</i> , 2010 , 6, 527-533	16.2	223
603	Improved performance of 1.3 μ m multilayer InAs quantum-dot lasers using a high-growth-temperature GaAs spacer layer. <i>Applied Physics Letters</i> , 2004 , 85, 704-706	3.4	221
602	Damping of exciton Rabi rotations by acoustic phonons in optically excited InGaAs/GaAs quantum dots. <i>Physical Review Letters</i> , 2010 , 104, 017402	7.4	219
601	Exciton-light coupling in single and coupled semiconductor microcavities: Polariton dispersion and polarization splitting. <i>Physical Review B</i> , 1999 , 59, 5082-5089	3.3	213
600	Observation of bright polariton solitons in a semiconductor microcavity. <i>Nature Photonics</i> , 2012 , 6, 50-55	33.9	204
599	Parametric oscillation in a vertical microcavity: A polariton condensate or micro-optical parametric oscillation. <i>Physical Review B</i> , 2000 , 62, R16247-R16250	3.3	204
598	Photon-mediated hybridization of frenkel excitons in organic semiconductor microcavities. <i>Science</i> , 2000 , 288, 1620-3	33.3	189
597	Determination of the shape and indium distribution of low-growth-rate InAs quantum dots by cross-sectional scanning tunneling microscopy. <i>Applied Physics Letters</i> , 2002 , 81, 1708-1710	3.4	184

596	Chirality of nanophotonic waveguide with embedded quantum emitter for unidirectional spin transfer. <i>Nature Communications</i> , 2016 , 7, 11183	17.4	158
595	Charged and neutral exciton complexes in individual self-assembled In(Ga)As quantum dots. <i>Physical Review B</i> , 2001 , 63,	3.3	158
594	Inversion of exciton level splitting in quantum dots. <i>Physical Review B</i> , 2005 , 72,	3.3	157
593	Strong exciton-photon coupling in a low-Q all-metal mirror microcavity. <i>Applied Physics Letters</i> , 2002 , 81, 3519-3521	3.4	157
592	Optimizing the growth of 1.3 μm InAs/InGaAs dots-in-a-well structure. <i>Journal of Applied Physics</i> , 2003 , 93, 2931-2936	2.5	154
591	Polariton condensation in dynamic acoustic lattices. <i>Physical Review Letters</i> , 2010 , 105, 116402	7.4	152
590	Phonon-induced Rabi-frequency renormalization of optically driven single InGaAs/GaAs quantum dots. <i>Physical Review Letters</i> , 2010 , 105, 177402	7.4	152
589	Electronic energy levels and energy relaxation mechanisms in self-organized InAs/GaAs quantum dots. <i>Physical Review B</i> , 1996 , 54, 17738-17744	3.3	152
588	Investigation of InGaAs-InP quantum wells by optical spectroscopy. <i>Semiconductor Science and Technology</i> , 1986 , 1, 29-40	1.8	148
587	Long lifetimes of quantum-dot intersublevel transitions in the terahertz range. <i>Nature Materials</i> , 2009 , 8, 803-7	27	137
586	Emission spectra and mode structure of InAs/GaAs self-organized quantum dot lasers. <i>Applied Physics Letters</i> , 1998 , 73, 969-971	3.4	134
585	Observation of multicharged excitons and biexcitons in a single InGaAs quantum dot. <i>Physical Review B</i> , 2001 , 63,	3.3	132
584	Relaxation bottleneck and its suppression in semiconductor microcavities. <i>Physical Review B</i> , 2000 , 62, R2283-R2286	3.3	131
583	Photonic band-structure effects in the reflectivity of periodically patterned waveguides. <i>Physical Review B</i> , 1999 , 60, R16255-R16258	3.3	131
582	Valley-addressable polaritons in atomically thin semiconductors. <i>Nature Photonics</i> , 2017 , 11, 497-501	33.9	127
581	Motional Narrowing in Semiconductor Microcavities. <i>Physical Review Letters</i> , 1996 , 77, 4792-4795	7.4	126
580	Intrinsic decoherence mechanisms in the microcavity polariton condensate. <i>Physical Review Letters</i> , 2008 , 101, 067404	7.4	123
579	New physics and devices based on self-assembled semiconductor quantum dots. <i>Journal Physics D: Applied Physics</i> , 2005 , 38, 2059-2076	3	122

578	Fast optical preparation, control, and readout of a single quantum dot spin. <i>Physical Review Letters</i> , 2008 , 100, 197401	7.4	120
577	Nuclear spin switch in semiconductor quantum dots. <i>Physical Review Letters</i> , 2007 , 98, 026806	7.4	117
576	Long-wavelength light emission and lasing from InAs/GaAs quantum dots covered by a GaAsSb strain-reducing layer. <i>Applied Physics Letters</i> , 2005 , 86, 143108	3.4	111
575	Two-dimensional metal-chalcogenide films in tunable optical microcavities. <i>Nano Letters</i> , 2014 , 14, 7003-8.5	8.5	109
574	Exciton-polariton gap solitons in two-dimensional lattices. <i>Physical Review Letters</i> , 2013 , 111, 146401	7.4	108
573	Resonant coupling of near-infrared radiation to photonic band structure waveguides. <i>Journal of Lightwave Technology</i> , 1999 , 17, 2050-2057	4	108
572	High Purcell factor generation of indistinguishable on-chip single photons. <i>Nature Nanotechnology</i> , 2018 , 13, 835-840	28.7	105
571	Fine structure of charged and neutral excitons in InAs-Al _{0.6} Ga _{0.4} As quantum dots. <i>Physical Review B</i> , 2002 , 66,	3.3	103
570	Off-branch polaritons and multiple scattering in semiconductor microcavities. <i>Physical Review B</i> , 2001 , 64,	3.3	103
569	Electric-field and temperature tuning of exciton-photon coupling in quantum microcavity structures. <i>Physical Review B</i> , 1995 , 51, 2600-2603	3.3	102
568	High-performance three-layer 1.3- μm InAs-GaAs quantum-dot lasers with very low continuous-wave room-temperature threshold currents. <i>IEEE Photonics Technology Letters</i> , 2005 , 17, 1139-1141	2.2	101
567	Quantum-confined Stark shifts of charged exciton complexes in quantum dots. <i>Physical Review B</i> , 2004 , 70,	3.3	99
566	SELF-ASSEMBLED SEMICONDUCTOR QUANTUM DOTS: Fundamental Physics and Device Applications. <i>Annual Review of Materials Research</i> , 2004 , 34, 181-218	12.8	98
565	An investigation of the deep level photoluminescence spectra of InP(Mn), InP(Fe), and of undoped InP. <i>Journal of Applied Physics</i> , 1982 , 53, 4955-4963	2.5	97
564	Phonon-assisted population inversion of a single InGaAs/GaAs quantum dot by pulsed laser excitation. <i>Physical Review Letters</i> , 2015 , 114, 137401	7.4	96
563	Interplay of order and disorder in the optical properties of opal photonic crystals. <i>Physical Review B</i> , 2002 , 66,	3.3	95
562	Intraband relaxation via polaron decay in InAs self-assembled quantum dots. <i>Physical Review B</i> , 2004 , 70,	3.3	94
561	Interfacing spins in an InGaAs quantum dot to a semiconductor waveguide circuit using emitted photons. <i>Physical Review Letters</i> , 2013 , 110, 037402	7.4	91

560	Coherent optical control of the spin of a single hole in an InAs/GaAs quantum dot. <i>Physical Review Letters</i> , 2012 , 108, 017402	7.4	90
559	Stimulated spin dynamics of polaritons in semiconductor microcavities. <i>Physical Review B</i> , 2002 , 65,	3.3	88
558	Mode structure of the L3 photonic crystal cavity. <i>Applied Physics Letters</i> , 2007 , 90, 241117	3.4	85
557	Electron-phonon interactions in indium gallium arsenide. <i>Semiconductor Science and Technology</i> , 1987 , 2, 329-336	1.8	85
556	An investigation of the anisotropy of the valence band of GaAs by cyclotron resonance. <i>Journal of Physics C: Solid State Physics</i> , 1976 , 9, 2809-2821		85
555	Direct measurement of the hole-nuclear spin interaction in single InP/GaN quantum dots using photoluminescence spectroscopy. <i>Physical Review Letters</i> , 2011 , 106, 027402	7.4	84
554	Enhanced phonon-assisted absorption in single InAs/GaAs quantum dots. <i>Physical Review B</i> , 2001 , 63,	3.3	84
553	Transition from strong to weak coupling and the onset of lasing in semiconductor microcavities. <i>Physical Review B</i> , 2002 , 65,	3.3	83
552	Exciton Polaritons in a Two-Dimensional Lieb Lattice with Spin-Orbit Coupling. <i>Physical Review Letters</i> , 2018 , 120, 097401	7.4	82
551	Experimental study of light emission from strongly coupled organic semiconductor microcavities following nonresonant laser excitation. <i>Physical Review B</i> , 2002 , 65,	3.3	81
550	Electric-field-dependent carrier capture and escape in self-assembled InAs/GaAs quantum dots. <i>Applied Physics Letters</i> , 2000 , 77, 4344-4346	3.4	77
549	Electronic processes in double-barrier resonant-tunneling structures studied by photoluminescence spectroscopy in zero and finite magnetic fields. <i>Physical Review B</i> , 1990 , 41, 10754-10766	3.3	75
548	Influences of the spacer layer growth temperature on multilayer InAs/GaAs quantum dot structures. <i>Journal of Applied Physics</i> , 2004 , 96, 1988-1992	2.5	74
547	Effect of thermal annealing and strain engineering on the fine structure of quantum dot excitons. <i>Physical Review B</i> , 2004 , 70,	3.3	73
546	p-doped 1.3 μm InAs/GaAs quantum-dot laser with a low threshold current density and high differential efficiency. <i>Applied Physics Letters</i> , 2006 , 89, 073113	3.4	72
545	Photocurrent spectroscopy of InAs/GaAs self-assembled quantum dots. <i>Physical Review B</i> , 2000 , 62, 16784-16791	3.4	71
544	Photoluminescence decay time measurements from self-organized InAs/GaAs quantum dots. <i>Journal of Applied Physics</i> , 1999 , 86, 2555-2561	2.5	72
543	Electroluminescence from a conjugated polymer microcavity structure. <i>Applied Physics Letters</i> , 1995 , 67, 1355-1357	3.4	72

542	Optical properties of undoped organometallic grown ZnSe and ZnS. <i>Journal of Crystal Growth</i> , 1982 , 59, 301-306	1.6	72
541	Rotation of the plane of polarization of light in a semiconductor microcavity. <i>Physical Review B</i> , 2006 , 73,	3.3	70
540	Free-carrier screening of the interaction between excitons and longitudinal-optical phonons in In _x Ga _{1-x} As-InP quantum wells. <i>Physical Review B</i> , 1987 , 35, 5925-5928	3.3	70
539	Far infrared photoconductivity from majority and minority impurities in high purity Si and Ge. <i>Solid State Communications</i> , 1974 , 15, 1403-1408	1.6	70
538	Photoluminescence, photoluminescence excitation, and resonant Raman spectroscopy of disordered and ordered Ga _{0.52} In _{0.48} P. <i>Journal of Applied Physics</i> , 1993 , 73, 5163-5172	2.5	69
537	Hole mass measurement in p-type InP and GaP by submillimetre cyclotron resonance in pulsed magnetic fields. <i>Solid State Communications</i> , 1974 , 15, 693-697	1.6	69
536	Polarization bistability and resultant spin rings in semiconductor microcavities. <i>Physical Review Letters</i> , 2010 , 105, 216402	7.4	68
535	Ultrafast nonlinear response of AlGaAs two-dimensional photonic crystal waveguides. <i>Applied Physics Letters</i> , 2003 , 83, 851-853	3.4	68
534	Tailoring of internal fields in InGaAs/GaAs multiwell structures grown on (111)B GaAs. <i>Applied Physics Letters</i> , 1993 , 63, 752-754	3.4	67
533	Phonon coupling and X- Gamma mixing in GaAs-AlAs short-period superlattices. <i>Physical Review B</i> , 1989 , 39, 11191-11194	3.3	67
532	InGaAs-InP multiple quantum wells grown by atmospheric pressure metalorganic chemical vapor deposition. <i>Applied Physics Letters</i> , 1987 , 51, 24-26	3.4	67
531	Dynamics of coherent and incoherent spin polarizations in ensembles of quantum dots. <i>Physical Review Letters</i> , 2004 , 93, 057401	7.4	66
530	Donor discrimination and bound exciton spectra in InP. <i>Journal of Applied Physics</i> , 1983 , 54, 346-359	2.5	65
529	Comparative study of InGaAs quantum dot lasers with different degrees of dot layer confinement. <i>Applied Physics Letters</i> , 2002 , 81, 1-3	3.4	64
528	Asymmetric angular emission in semiconductor microcavities. <i>Physical Review B</i> , 2000 , 62, R13278-R13283	3.3	64
527	Strongly polarized bound exciton luminescence from GaAs grown by molecular beam epitaxy. <i>Applied Physics Letters</i> , 1985 , 46, 427-429	3.4	64
526	Coexisting nonequilibrium condensates with long-range spatial coherence in semiconductor microcavities. <i>Physical Review B</i> , 2009 , 80,	3.3	63
525	Ultra-low-power hybrid light-matter solitons. <i>Nature Communications</i> , 2015 , 6, 8317	17.4	62

524	Electroluminescence emission from polariton states in GaAs-based semiconductor microcavities. <i>Applied Physics Letters</i> , 2008 , 92, 061107	3.4	62
523	Element-sensitive measurement of the hole-nuclear spin interaction in quantum dots. <i>Nature Physics</i> , 2013 , 9, 74-78	16.2	61
522	Photoluminescence study of the density-of-states between Landau levels in the quantum hall effect system. <i>Solid State Communications</i> , 1988 , 67, 637-641	1.6	61
521	Heavy photon dispersions in photonic crystal waveguides. <i>Applied Physics Letters</i> , 2000 , 77, 178-180	3.4	60
520	Electrical and spectroscopic studies of space-charged buildup, energy relaxation and magnetically enhanced bistability in resonant-tunneling structures. <i>Solid-State Electronics</i> , 1989 , 32, 1101-1108	1.7	60
519	Optical and capacitance spectroscopy of InP:Fe. <i>Journal of Physics C: Solid State Physics</i> , 1981 , 14, 5069-5079		58
518	Waveguide coupled resonance fluorescence from on-chip quantum emitter. <i>Nano Letters</i> , 2014 , 14, 6997-7002	1.9	57
517	Continuum transitions and phonon coupling in single self-assembled Stranski-Krastanow quantum dots. <i>Physical Review B</i> , 2003 , 68,	3.3	57
516	Excited states and selection rules in self-assembled InAs/GaAs quantum dots. <i>Physical Review B</i> , 1999 , 60, R2185-R2188	3.3	57
515	Hybrid organic-inorganic exciton-polaritons in a strongly coupled microcavity. <i>Physical Review B</i> , 2006 , 74,	3.3	56
514	Manipulation of the homogeneous linewidth of an individual In(Ga)As quantum dot. <i>Physical Review B</i> , 2002 , 66,	3.3	56
513	Experimental determination of Gamma -X intervalley transfer mechanisms in GaAs/AlAs heterostructures. <i>Physical Review B</i> , 1996 , 54, R8329-R8332	3.3	55
512	Nonlinear polaritons in a monolayer semiconductor coupled to optical bound states in the continuum. <i>Light: Science and Applications</i> , 2020 , 9, 56	16.7	55
511	Spin Textures of Exciton-Polaritons in a Tunable Microcavity with Large TE-TM Splitting. <i>Physical Review Letters</i> , 2015 , 115, 246401	7.4	54
510	Vacuum Rabi coupling enhancement and Zeeman splitting in semiconductor quantum microcavity structures in a high magnetic field. <i>Physical Review B</i> , 1996 , 53, R10469-R10472	3.3	54
509	Pumping of nuclear spins by optical excitation of spin-forbidden transitions in a quantum dot. <i>Physical Review Letters</i> , 2010 , 104, 066804	7.4	53
508	Stacked low-growth-rate InAs quantum dots studied at the atomic level by cross-sectional scanning tunneling microscopy. <i>Applied Physics Letters</i> , 2003 , 82, 3758-3760	3.4	53
507	Fermi-energy-edge singularity in quantum wells containing more than one occupied subband. <i>Physical Review B</i> , 1991 , 43, 7354-7357	3.3	53

506	Structural analysis of strained quantum dots using nuclear magnetic resonance. <i>Nature Nanotechnology</i> , 2012 , 7, 646-50	28.7	52
505	Effect of interactions on vortices in a nonequilibrium polariton condensate. <i>Physical Review Letters</i> , 2010 , 104, 126402	7.4	52
504	Individual neutral and charged In _x Ga _{1-x} As/GaAs quantum dots with strong in-plane optical anisotropy. <i>Physical Review B</i> , 2005 , 72,	3.3	52
503	Cavity-polariton dispersion and polarization splitting in single and coupled semiconductor microcavities. <i>Physics of the Solid State</i> , 1999 , 41, 1223-1238	0.8	52
502	Electronic band structure of AlGaInP grown by solid-source molecular-beam epitaxy. <i>Applied Physics Letters</i> , 1994 , 65, 213-215	3.4	52
501	Self-organization of multiple polariton-polariton scattering in semiconductor microcavities. <i>Physical Review B</i> , 2008 , 77,	3.3	51
500	Many body shakeup in quantum well luminescence spectra. <i>Physical Review Letters</i> , 1993 , 70, 3115-3118	7.4	51
499	Suppressed Polariton Scattering in Semiconductor Microcavities. <i>Physical Review Letters</i> , 1998 , 81, 661-664	6.4	50
498	Optically induced splitting of bright excitonic states in coupled quantum microcavities. <i>Physical Review B</i> , 1998 , 57, 14877-14881	3.3	50
497	Two-qubit conditional quantum-logic operation in a single self-assembled quantum dot. <i>Physical Review B</i> , 2008 , 78,	3.3	49
496	Raman scattering in strongly coupled organic semiconductor microcavities. <i>Physical Review B</i> , 2001 , 63,	3.3	48
495	Direct observation of fine structure in the concentration of the deep donor [EL2] and its correlation with dislocations in undoped, semi-insulating GaAs. <i>Journal of Applied Physics</i> , 1984 , 56, 1109-1118	2.5	48
494	Dark Solitons in High Velocity Waveguide Polariton Fluids. <i>Physical Review Letters</i> , 2017 , 119, 097403	7.4	47
493	Polarization-dependent phenomena in the reflectivity spectra of semiconductor quantum microcavities. <i>Physical Review B</i> , 1997 , 56, R10032-R10035	3.3	47
492	Piezoelectric-field effects on transition energies, oscillator strengths, and level widths in (111)B-grown (In,Ga)As/GaAs multiple quantum wells. <i>Physical Review B</i> , 1993 , 48, 8491-8494	3.3	47
491	Mode structure of coupled L3 photonic crystal cavities. <i>Optics Express</i> , 2011 , 19, 5670-5	3.3	45
490	Suppression of Zeeman splitting of the energy levels of exciton-polariton condensates in semiconductor microcavities in an external magnetic field. <i>Physical Review Letters</i> , 2011 , 106, 257401	7.4	45
489	Effects of spin-dependent interactions on polarization of bright polariton solitons. <i>Physical Review Letters</i> , 2014 , 112, 046403	7.4	44

488	Dependence of stimulated scattering in semiconductor microcavities on pump power, angle, and energy. <i>Physical Review B</i> , 2003 , 68,	3-3	44
487	Optical properties of InGaAs-InP single quantum wells grown by atmospheric pressure metalorganic chemical vapor deposition. <i>Applied Physics Letters</i> , 1986 , 48, 1455-1457	3-4	44
486	Dominant effect of polariton-polariton interactions on the coherence of the microcavity optical parametric oscillator. <i>Physical Review Letters</i> , 2006 , 97, 097402	7-4	43
485	Recent progress in polymers for electroluminescence: microcavity devices and electron transport polymers. <i>Thin Solid Films</i> , 1996 , 273, 39-47	2-2	43
484	Optical orientation and control of spin memory in individual InGaAs quantum dots. <i>Physical Review B</i> , 2005 , 72,	3-3	42
483	Band gap of Γ completely disorderedGa0.52In0.48P. <i>Applied Physics Letters</i> , 1995 , 66, 3185-3187	3-4	42
482	Diamagnetism as a probe of exciton localization in quantum wells. <i>Physical Review B</i> , 1989 , 39, 10943-10954	3-4	42
481	Excitation mechanisms of photoluminescence in double-barrier resonant-tunneling structures. <i>Physical Review B</i> , 1990 , 42, 3069-3076	3-3	42
480	Photoinduced quenching of infrared absorption nonuniformities of large diameter GaAs crystals. <i>Applied Physics Letters</i> , 1984 , 44, 447-449	3-4	42
479	Monolithic integration of a quantum emitter with a compact on-chip beam-splitter. <i>Applied Physics Letters</i> , 2014 , 104, 231107	3-4	41
478	Magneto-optical studies of self-organized InAs/GaAs quantum dots. <i>Physical Review B</i> , 1998 , 57, R2073-R2076	3-3	41
477	Ring emission and exciton-pair scattering in semiconductor microcavities. <i>Physical Review B</i> , 2002 , 65,	3-3	41
476	Polariton-induced optical asymmetry in semiconductor microcavities. <i>Physical Review B</i> , 1998 , 58, 15367-15370	3-3	41
475	Exciton polaritons in semiconductor waveguides. <i>Applied Physics Letters</i> , 2013 , 102, 012109	3-4	40
474	Strong exciton-photon coupling in open semiconductor microcavities. <i>Applied Physics Letters</i> , 2014 , 104, 192107	3-4	40
473	Low threshold current density and negative characteristic temperature 1.3 μ m InAs self-assembled quantum dot lasers. <i>Applied Physics Letters</i> , 2007 , 90, 111102	3-4	39
472	Growth and characterisation of quantum wells and selectively doped heterostructures of InP/Ga0.47In0.53As grown by solid source MBE. <i>Journal of Crystal Growth</i> , 1987 , 81, 288-295	1-6	39
471	Beating of exciton-dressed states in a single semiconductor InGaAs/GaAs quantum dot. <i>Physical Review Letters</i> , 2009 , 102, 207401	7-4	38

- 470 Polariton parametric scattering processes in semiconductor microcavities observed in continuous wave experiments. *Physical Review B*, **2002**, 65, 3-3 38
- 469 The complex form of donor energy levels in gallium phosphide. *Journal of Physics C: Solid State Physics*, **1977**, 10, 5111-5129 38
- 468 Highly nonlinear trion-polaritons in a monolayer semiconductor. *Nature Communications*, **2020**, 11, 3589 17.4 38
- 467 Restoring mode degeneracy in H1 photonic crystal cavities by uniaxial strain tuning. *Applied Physics Letters*, **2012**, 100, 121116 3-4 37
- 466 Carrier lifetimes in type-II InAs quantum dots capped with a GaAsSb strain reducing layer. *Applied Physics Letters*, **2008**, 92, 251905 3-4 37
- 465 Engineering carrier confinement potentials in 1.3- μm InAs/GaAs quantum dots with InAlAs layers: Enhancement of the high-temperature photoluminescence intensity. *Applied Physics Letters*, **2003**, 83, 3716-3718 3-4 37
- 464 Electroreflectance spectroscopy from quantum well structures in an electric field. *Journal of Physics C: Solid State Physics*, **1986**, 19, 857-871 37
- 463 The growth by MOCVD using new group VI sources and assessment by HRTEM and CL of Zn-based II-VI single crystal layers. *Journal of Crystal Growth*, **1985**, 72, 17-22 1.6 37
- 462 Time resolved DC electroluminescence studies in ZnS:Mn, Cu powder phosphors. *Journal Physics D: Applied Physics*, **1981**, 14, 301-322 3 37
- 461 Angular-dependent magnetoluminescence study of the layer compound 2H-PbI₂. *Physical Review B*, **1978**, 18, 7080-7088 3-3 37
- 460 Properties of the electron-hole liquid in GaP. *Physical Review B*, **1979**, 19, 2231-2245 3-3 37
- 459 Valley coherent exciton-polaritons in a monolayer semiconductor. *Nature Communications*, **2018**, 9, 4797 17.4 37
- 458 Suppression of nuclear spin bath fluctuations in self-assembled quantum dots induced by inhomogeneous strain. *Nature Communications*, **2015**, 6, 6348 17.4 36
- 457 Polarized quantum dot emission from photonic crystal nanocavities studied under moderate resonant enhanced excitation. *Optics Express*, **2007**, 15, 17221-30 3-3 36
- 456 Structural and optical studies of vertically aligned InAs/GaAs self-assembled quantum dots. *Journal of Applied Physics*, **2001**, 90, 6374-6378 2.5 36
- 455 Spatial structure and stability of the macroscopically occupied polariton state in the microcavity optical parametric oscillator. *Physical Review B*, **2006**, 73, 3-3 35
- 454 Strong coupling in high-finesse organic semiconductor microcavities. *Applied Physics Letters*, **2003**, 83, 5377-5379 3-4 35
- 453 Nonlinearities in emission from the lower polariton branch of semiconductor microcavities. *Physical Review B*, **1999**, 60, R11293-R11296 3-3 35

452	Fast preparation of a single-hole spin in an InAs/GaAs quantum dot in a Voigt-geometry magnetic field. <i>Physical Review B</i> , 2012 , 85,	3.3	34
451	Observation of an Electron-Hole Liquid in Cubic SiC. <i>Physical Review Letters</i> , 1978 , 40, 56-60	7.4	34
450	Homogeneous array of nanowire-embedded quantum light emitters. <i>Nano Letters</i> , 2013 , 13, 861-5	11.5	33
449	Control of polarized single quantum dot emission in high-quality-factor microcavity pillars. <i>Applied Physics Letters</i> , 2006 , 88, 051113	3.4	33
448	Recombination and loss mechanisms in low-threshold InAs-GaAs 1.3- μm quantum-dot lasers. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2005 , 11, 1041-1047	3.8	33
447	Control of photoluminescence emission from a conjugated polymer using an optimised microactivity structure. <i>Chemical Physics Letters</i> , 1996 , 263, 655-660	2.5	33
446	Wannier-Stark localization of X and Gamma states in GaAs-AlAs short-period superlattices. <i>Physical Review B</i> , 1990 , 42, 3591-3598	3.3	33
445	Transition metal diffusion in InP: Photoluminescence investigation. <i>Journal of Applied Physics</i> , 1984 , 55, 2951-2961	2.5	33
444	Submillimetre cyclotron resonance of electrons in GaP. <i>Solid State Communications</i> , 1975 , 16, 363-366	1.6	33
443	Exciton polaritons in semiconductor quantum microcavities in a high magnetic field. <i>Physical Review B</i> , 1997 , 55, 16395-16403	3.3	32
442	Giant enhancement of polariton relaxation in semiconductor microcavities by polariton-free carrier interaction: Experimental evidence and theory. <i>Physical Review B</i> , 2003 , 67,	3.3	32
441	Identification of donors in vapor grown indium phosphide. <i>Journal of Applied Physics</i> , 1984 , 55, 957-963	2.5	32
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